

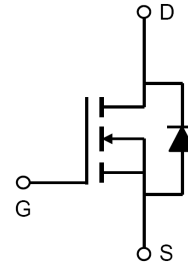
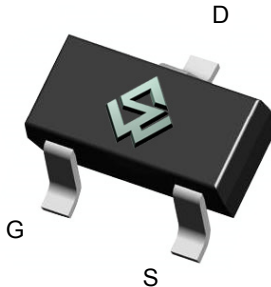
**20V Single N-Channel Enhancement-Mode MOSFET****General Description**

- Low gate charge.
- Use as a load switch.
- Use in PWM applications

Product Summary

- BV_{DSS} 20V
- $R_{DS(on)}$ @VGS = 4.5V < 40mΩ
- $R_{DS(on)}$ @VGS = 2.5V < 50mΩ

SOT-23

**Absolute Maximum Ratings** ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current ($T_A=25^\circ\text{C}$)	I_D	3.0	A
Drain Current ($T_A=75^\circ\text{C}$)		1.2	A
Pulsed Drain Current ^a	I_{DM}	12	A
Power Dissipation ^b ($T_A=25^\circ\text{C}$)	P_D	1.25	W
Power Dissipation ^b ($T_A=75^\circ\text{C}$)		1.0	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Junction-to-Ambient ^a ($t \leq 10\text{s}$)	$R_{\theta JA}$	100	°C/W
Junction-to-Ambient ^{a,d} (Steady-State)		130	°C/W
Junction-to-Lead (Steady-State)	$R_{\theta JL}$	90	°C/W

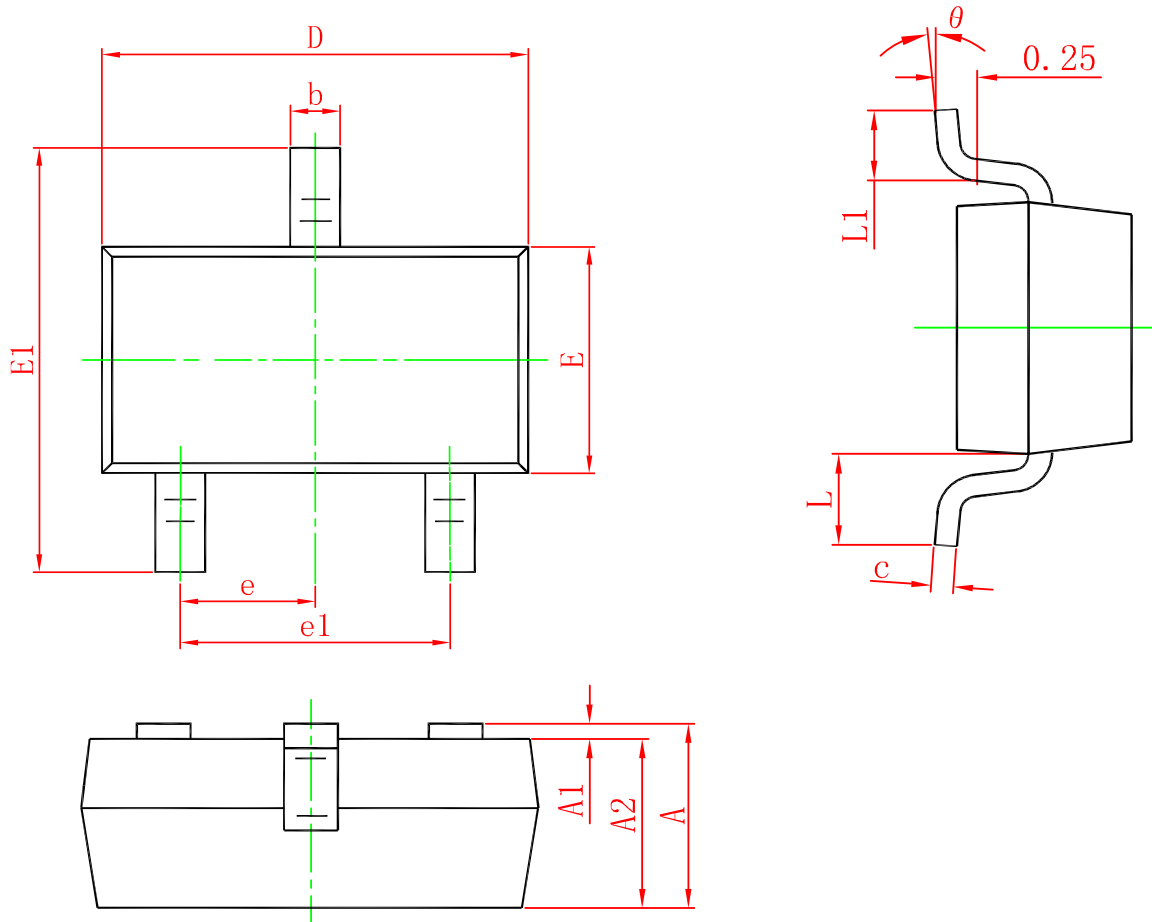


Electrical Characteristics (T _A = 25°C unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} = 0V , I _D = 250uA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20V , V _{GS} = 0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±8V , V _{DS} = 0V			±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250uA	0.5		1.0	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} = 4.5V , I _D = 3.0A			40	mΩ
		V _{GS} = 2.5V , I _D = 1.5A			50	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 2.5V , I _D = 3.0A		20		S
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} = 0V , I _S = 1.0A			1.2	V
I _S	Maximum Body-Diode Continuous Current				2.0	A
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 10V , V _{GS} = 0V f = 1.0MHz		485		pF
C _{oss}	Output Capacitance			31		pF
C _{rss}	Reverse Transfer Capacitance			20		pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} = 10V , I _D = 3.0A V _{GS} = 6V		25		nC
Q _{gs}	Gate-Source Charge			1.8		nC
Q _{gd}	Gate-Drain Charge			1.3		nC
t _{D(ON)}	Turn-On Delay Time	V _{DD} = 10V , I _D = 1A V _{GS} = 6V R _{GEN} = 6 ohm		16		ns
t _r	Turn-On Rise Time			28		ns
t _{D(OFF)}	Turn-Off Delay Time			45		ns
t _f	Turn-Off Fall Time			26		ns

- a. Repetitive rating, Pulse width limited by junction temperature T_{J(MAX)}=150 °C. Ratings are based on low frequency and duty cycles to keep initial T_J=25 °C
- b. The power dissipation P_D is based on T_{J(MAX)}=150 °C , using ≤10s junction-to-ambient thermal resistance.
- c. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design.
- d. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.



SOT-23 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.	0.022 REF.		
θ	0.300	0.500	0.012	0.020

单击下面可查看定价，库存，交付和生命周期等信息

[>>SiliconWisdom\(矽睿半导体\)](#)